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From: Jerome W. Massie	Date: February 24, 2004	No. of Pages: 3 (including this page)	Application No. 09/504,782
Comments: <p>Mr. Ip:</p> <p>Attached please find a copy of the Proposed Amendments in compliance with 37 CFR 1.312, that the client would like to submit.</p> <p>Thanks</p> <p>Jerome W. Massie Registration No. 38,118</p>			

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From: Jerome W. Massie	Date: February 24, 2004	No. of Pages: 3 (including this page)	Client/Matter: 740819-337
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Your Ref.: 740819-337

Our Ref.: M99-G-192U51

INSTRUCTIONS

Please amend the claims under 37 C.F.R 1.312 as follows:

1. (Third amended)

A semiconductor laser device comprising:

a first cladding layer, which is made of a nitride semiconductor of a first conductivity type and is formed over substrate;

an active layer, which is made of $\text{In}_y\text{Ga}_{1-y}\text{N}$ and is formed over the first cladding layer;

a second cladding layer, which is made of still another nitride semiconductor of a second conductivity type and is formed over the active layer; and

an spontaneous-emission-absorbing layer, which is made of $\text{In}_x\text{Ga}_{1-x}\text{N}$ of the first conductivity type and has an energy gap as an absorbing spontaneous emission layer for emission from the active layer, is formed the substrate and the first cladding layer,

wherein $0 < x < 1$, $0 < y < 1$ and $x = y$ in the composition of In .

2. (Twice amended)

The device of claim 1, wherein the spontaneous-emission-absorbing layer is formed in contact with the first cladding layer.

3. (Twice amended)

The device of claim 1, wherein the spontaneous-emission-absorbing layer is formed in contact with the substrate.

4. (Third Amended)

A semiconductor laser device comprising:

a first cladding layer, which is made of a nitride semiconductor of a first conductivity type and is formed over

substrate;

an active layer, which is made of $\text{In}_x\text{Ga}_{1-y}\text{N}$ and is formed over the first cladding layer;

a second cladding layer, which is made of still another nitride semiconductor of a second conductivity type and is formed over the active layer;

an electrode formed over the second cladding layer; and

an spontaneous-emission-absorbing layer, which is made of $\text{In}_x\text{Ga}_{1-y}\text{N}$ of the second conductivity type and has an energy gap as an absorbing spontaneous emission layer for emission from the active layer, is formed the second cladding layer and the electrode,

wherein $0 < x < 1$, $0 < y < 1$ and $x + y$ in the composition of In .

5. (Twice amended)

The device of Claim 4, wherein the spontaneous-emission-absorbing layer is formed in contact with the second cladding layer.

6. (Twice amended)

The device of Claim 4, wherein the spontaneous-emission-absorbing layer is formed in contact with the electrode.

7.-30. (Cancelled)